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Data Sheet

September 2013

# N-Channel Logic Level Power MOSFET 60V, 11A, 107 $m\Omega$

These N-Channel enhancement-mode power MOSFETs are manufactured using the latest manufacturing process technology. This process, which uses feature sizes approaching those of LSI circuits, gives optimum utilization of silicon, resulting in outstanding performance. They were designed for use in applications such as switching regulators, switching converters, motor drivers and relay drivers. These transistors can be operated directly from integrated circuits.

Formerly developmental type TA49158.

#### **Ordering Information**

PART NUMBER	PACKAGE	BRAND
RFD3055LE	TO-251AA	F3055L
RFD3055LESM9A	TO-252AA	F3055L

#### **Features**

- 11A, 60V
- $r_{DS(ON)} = 0.107\Omega$
- Temperature Compensating PSPICE<sup>®</sup> Model
- Peak Current vs Pulse Width Curve
- UIS Rating Curve
- Related Literature
  - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

#### Symbol



#### Packaging

JEDEC TO-251AA



#### JEDEC TO-252AA



#### RFD3055LE, RFD3055LESM

### **Absolute Maximum Ratings** $T_C = 25^{\circ}C$ , Unless Otherwise Specified

	RFD3055LE,	
	RFD3055LESM9A	UNITS
Drain to Source Voltage (Note 1)	60	V
Drain to Gate Voltage ( $R_{GS} = 20k\Omega$ ) (Note 1) $V_{DGR}$	60	V
Gate to Source VoltageV <sub>GS</sub>	±16	V
Continuous Drain Current	11	Α
Pulsed Drain Current (Note 3)	Refer to Peak Current Curve	
Single Pulse Avalanche Rating	Refer to UIS Curve	
Power Dissipation	38	W
Derate Above 25 <sup>o</sup> C	0.25	W/oC
Operating and Storage Temperature	-55 to 175	°С
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10sT <sub>L</sub>	300	°C
Package Body for 10s, See Techbrief 334	260	°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

#### NOTE:

1.  $T_J = 25^{\circ}C$  to  $150^{\circ}C$ .

#### **Electrical Specifications** $T_C = 25^{\circ}C$ , Unless Otherwise Specified

PARAMETER	SYMBOL	TEST C	ONDITIONS	MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V		60	-	-	V
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$		1	-	3	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 55V, V_{GS} = 0V$		-	-	1	μΑ
	$V_{DS} = 50V, V_{GS} = 0V, T_{C} = 150^{\circ}C$		', T <sub>C</sub> = 150 <sup>o</sup> C	-	-	250	μΑ
Gate to Source Leakage Current	I <sub>GSS</sub>	$V_{GS} = \pm 16V$		-	-	±100	nA
Drain to Source On Resistance (Note 2)	r <sub>DS(ON)</sub>	I <sub>D</sub> = 8A, V <sub>GS</sub> = 5V (Fi	gure 11)	-	-	0.107	Ω
Turn-On Time	ton	$V_{DD} \approx 30V$ , $I_{D} = 8A$ , $V_{GS} = 4.5V$ , $R_{GS} = 32\Omega$ (Figures 10, 18, 19)		-	-	170	ns
Turn-On Delay Time	t <sub>d</sub> (ON)			-	8	-	ns
Rise Time	t <sub>r</sub>			-	105	-	ns
Turn-Off Delay Time	t <sub>d(OFF)</sub>			-	22	-	ns
Fall Time	t <sub>f</sub>			-	39	-	ns
Turn-Off Time	toff			-	-	92	ns
Total Gate Charge	Q <sub>g(TOT)</sub>	V <sub>GS</sub> = 0V to 10V	V <sub>DD</sub> = 30V, I <sub>D</sub> = 8A,	-	9.4	11.3	nC
Gate Charge at 5V	Q <sub>g(5)</sub>	V <sub>GS</sub> = 0V to 5V		-	5.2	6.2	nC
Threshold Gate Charge	Q <sub>g(TH)</sub>			-	0.36	0.43	nC
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1MHz (Figure 14)		-	350	-	pF
Output Capacitance	C <sub>OSS</sub>			-	105	-	pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			-	23	-	pF
Thermal Resistance Junction to Case	$R_{ heta JC}$			-	-	3.94	°C/W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	TO-220AB		-	- //	62	°C/W
		TO-251AA, TO-252AA	A	-	-	100	°C/W

#### **Source to Drain Diode Specifications**

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	V <sub>SD</sub>	I <sub>SD</sub> = 8A		-	1.25	V
Diode Reverse Recovery Time	t <sub>rr</sub>	$I_{SD} = 8A$ , $dI_{SD}/dt = 100A/\mu s$		-	66	ns

#### NOTES:

- 2. Pulse Test: Pulse Width  $\leq$  300ms, Duty Cycle  $\leq$  2%.
- 3. Repetitive Rating: Pulse Width limited by max junction temperature. See Transient Thermal Impedance Curve (Figure 3) and Peak Current Capability Curve (Figure 5).

#### Typical Performance Curves Unless Otherwise Specified

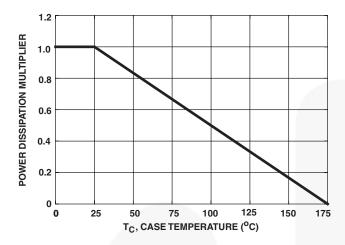


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

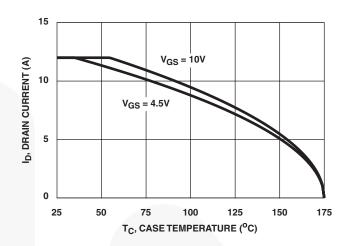


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

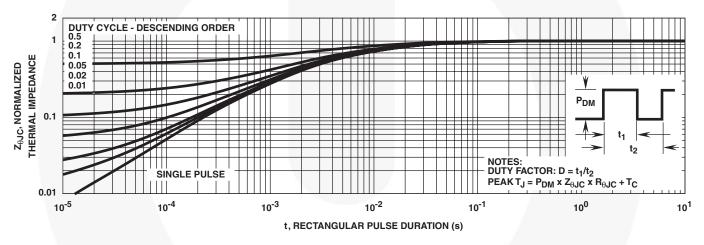


FIGURE 3. NORMALIZED TRANSIENT THERMAL IMPEDANCE

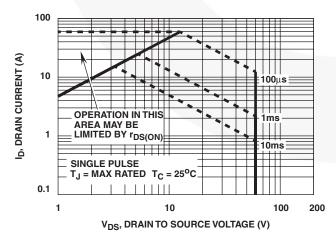


FIGURE 4. FORWARD BIAS SAFE OPERATING AREA

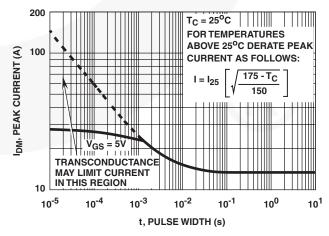
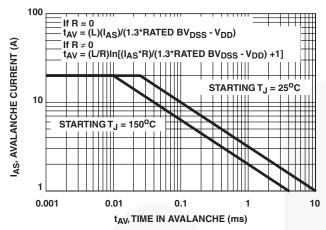


FIGURE 5. PEAK CURRENT CAPABILITY

#### Typical Performance Curves Unless Otherwise Specified (Continued)



NOTE: Refer to Fairchild Application Notes AN9321 and AN9322 FIGURE 6. UNCLAMPED INDUCTIVE SWITCHING

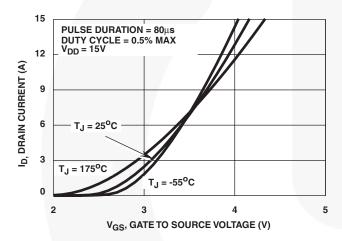


FIGURE 8. TRANSFER CHARACTERISTICS

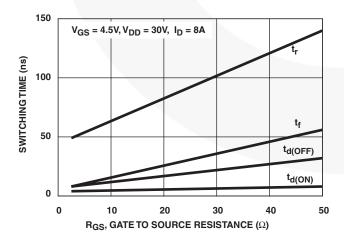


FIGURE 10. SWITCHING TIME vs GATE RESISTANCE

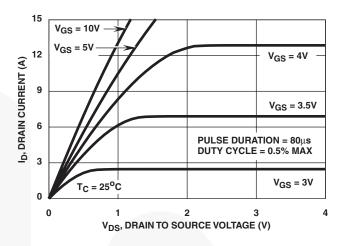


FIGURE 7. SATURATION CHARACTERISTICS

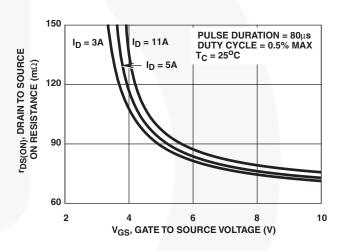


FIGURE 9. DRAIN TO SOURCE ON RESISTANCE vs GATE VOLTAGE AND DRAIN CURRENT

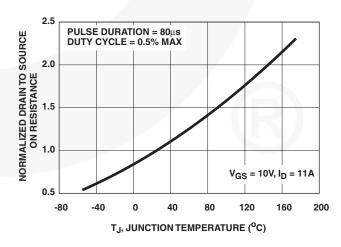


FIGURE 11. NORMALIZED DRAINTO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

#### Typical Performance Curves Unless Otherwise Specified (Continued)

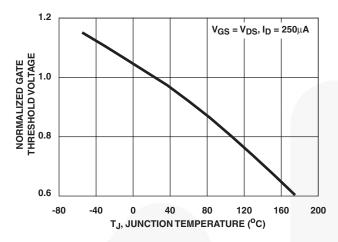


FIGURE 12. NORMALIZED GATE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE

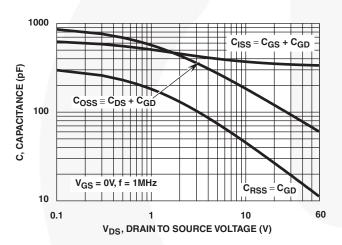


FIGURE 14. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE

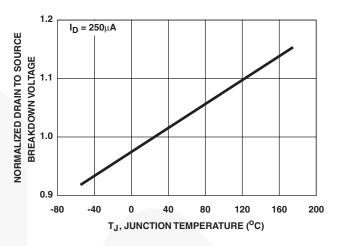
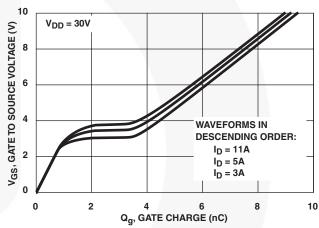


FIGURE 13. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE



NOTE: Refer to Fairchild Application Notes AN7254 and AN7260.

FIGURE 15. NORMALIZED SWITCHING WAVEFORMS FOR CONSTANT GATE CURRENT

#### Test Circuits and Waveforms

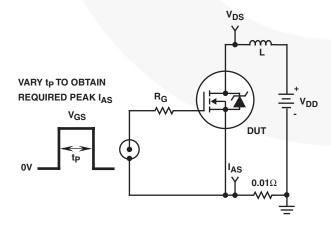


FIGURE 16. UNCLAMPED ENERGY TEST CIRCUIT

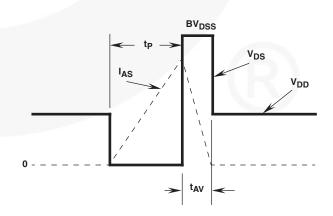


FIGURE 17. UNCLAMPED ENERGY WAVEFORMS

### Test Circuits and Waveforms (Continued)

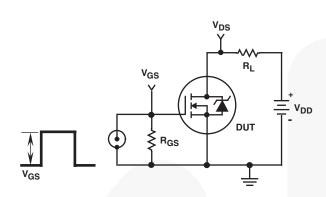


FIGURE 18. SWITCHING TEST CIRCUIT

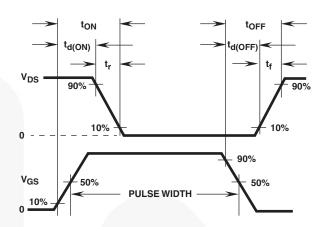


FIGURE 19. RESISTIVE SWITCHING WAVEFORMS

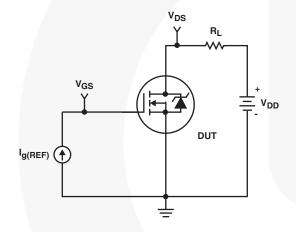


FIGURE 20. GATE CHARGE TEST CIRCUIT

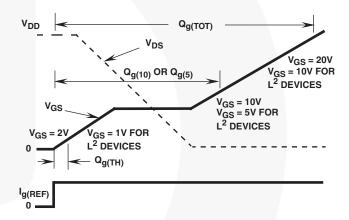


FIGURE 21. GATE CHARGE WAVEFORMS

#### **PSPICE Electrical Model**

rev 1/30/95

.SUBCKT RFD3055LE 2 1 3:

CA 12 8 3.9e-9 CB 15 14 4.9e-9 CIN 6 8 3.25e-10 DBODY 7 5 DBODYMOD LDRAIN DBREAK 5 11 DBREAKMOD **DPLCAP** DRAIN DPLCAP 10 5 DPLCAPMOD 10 RLDRAIN EBREAK 11 7 17 18 67.8 ≥RSLC1 **DBREAK** 51 EDS 14 8 5 8 1 RSLC2 ≥ EGS 13 8 6 8 1 **ESLC** ESG 6 10 6 8 1 11 EVTHRES 6 21 19 8 1 **EVTEMP 20 6 18 22 1** 50 DBODY RDRAIN <u>6</u> 8 **EBREAK** ESG IT 8 17 1 **EVTHRES** 16 21 19 8 **MWEAK** LDRAIN 2 5 1.0e-9 **LGATE EVTEMP** LGATE 1 9 5.42e-9 **RGATE** GATE 18 22 d₽ LSOURCE 3 7 2.57e-9 MMED 20 MSTRO RLGATE MMED 16 6 8 8 MMEDMOD LSOURCE MSTRO 16 6 8 8 MSTROMOD CIN SOURCE MWEAK 16 21 8 8 MWEAKMOD 8 **RSOURCE** RBREAK 17 18 RBREAKMOD 1 **RLSOURCE** RDRAIN 50 16 RDRAINMOD 3.7e-2 S1A <sup>o</sup>S2A RGATE 9 20 3.37 **RBREAK** 12 I RLDRAIN 2 5 10 15 13 8 14 13 **RLGATE 1 9 54.2** RLSOURCE 3 7 25.7 S1B RVTEMP o S2B RSLC1 5 51 RSLCMOD 1e-6 13 RSLC2 5 50 1e3 CB 19 CA IT RSOURCE 8 7 RSOURCEMOD 2.50e-2 14 **RVTHRES 22 8 RVTHRESMOD 1** VBAT <u>5</u> **EGS EDS** RVTEMP 18 19 RVTEMPMOD 1 8 S1A 6 12 13 8 S1AMOD S1B 13 12 13 8 S1BMOD **RVTHRES** S2A 6 15 14 13 S2AMOD S2B 13 15 14 13 S2BMOD VBAT 22 19 DC 1 ESLC 51 50 VALUE={(V(5,51)/ABS(V(5,51)))\*(PWR(V(5,51)/(1e-6\*30),3))} .MODEL DBODYMOD D (IS = 1.75e-13 RS = 1.75e-2 TRS1 = 1e-4 TRS2 = 5e-6 CJO = 5.9e-10 TT = 5.45e-8 N = 1.03 M = 0.6) .MODEL DBREAKMOD D (RS = 6.50e-1 TRS1 = 1.25e-4 TRS2 = 1.34e-6) .MODEL DPLCAPMOD D (CJO = 3.21e-10 IS = 1e-30 N = 10 M = 0.81) .MODEL MMEDMOD NMOS (VTO = 2.02 KP = .83 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u RG = 3.37) .MODEL MSTROMOD NMOS (VTO = 2.39 KP = 14 IS = 1e-30 N = 10 TOX = 1 L = 1 u W = 1 u) MODEL MWEAKMOD NMOS (VTO = 1.78 KP = 0.02 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u RG = 33.7 RS = 0.1) .MODEL RBREAKMOD RES (TC1 = 1.06e-3 TC2 = 0) MODEL RDRAINMOD RES (TC1 = 1.23e-2 TC2 = 2.58e-5) MODEL RSLCMOD RES (TC1 = 0 TC2 = 0) .MODEL RSOURCEMOD RES (TC1 = 1e-3 TC2 = 0) .MODEL RVTHRESMOD RES (TC1 = -2.19e-3 TC2 = -4.97e-6) .MODEL RVTEMPMOD RES (TC1 = -1.6e-3 TC2 = 1e-7) .MODEL S1AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -4 VOFF= -2.5) .MODEL S1BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -2.5 VOFF= -4)

For further discussion of the PSPICE model, consult **A New PSPICE Sub-Circuit for the Power MOSFET Featuring Global Temperature Options**; IEEE Power Electronics Specialist Conference Records, 1991, written by William J. Hepp and C. Frank Wheatley.

**FNDS** 

.MODEL S2AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -0.5 VOFF= 0) .MODEL S2BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = 0 VOFF= -0.5)



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